

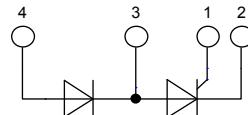
Thyristor

Phase leg

V_{RRM} = 1600 V
I_{T(AV)M} = 80 A
I_{T(RMS)} = 126 A

Part number

CMA 80 PD 1600 NA



Backside: isolated

E72873

Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

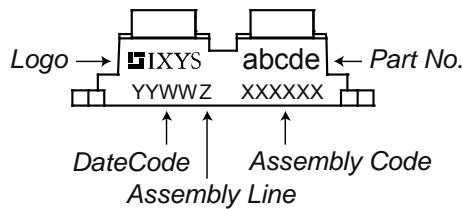
Package:

- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
V _{RSM/DSM}	max. non-repetitive reverse/forward blocking voltage	T _{VJ} = 25°C			1700	V
V _{RRM/DRM}	max. repetitive reverse/forward blocking voltage	T _{VJ} = 25°C			1600	V
I _{R/D}	reverse current, drain current	V _{R/D} = 1600 V	T _{VJ} = 25°C		100	µA
		V _{R/D} = 1600 V	T _{VJ} = 125°C		10	mA
V _T	forward voltage drop	I _T = 80 A	T _{VJ} = 25°C		1.30	V
		I _T = 160 A			1.64	V
		I _T = 80 A	T _{VJ} = 125°C		1.29	V
		I _T = 160 A			1.72	V
I _{T(AV)M}	average forward current	T _C = 80°C	T _{VJ} = 150°C		80	A
I _{T(RMS)}	RMS forward current	180° sine			126	A
V _{T0} r _T	threshold voltage slope resistance } for power loss calculation only		T _{VJ} = 150°C		0.86	V
					5.5	mΩ
R _{thJC}	thermal resistance junction to case				0.45	K/W
T _{VJ}	virtual junction temperature		-40		150	°C
P _{tot}	total power dissipation	T _C = 25°C			270	W
P _{GM}	max. gate power dissipation	t _G = 30 µs	T _C = 150°C		10	W
		t _G = 300 µs			5	W
P _{GAV}	average gate power dissipation				0.5	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	T _{VJ} = 45°C		1.07	kA
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V		1.16	kA
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C		910	A
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V		980	A
I ² t	value for fusing	t = 10 ms; (50 Hz), sine	T _{VJ} = 45°C		5.73	kA²s
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V		5.55	kA²s
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C		4.14	kA²s
		t = 8,3 ms; (60 Hz), sine	V _R = 0 V		4.00	kA²s
C _J	junction capacitance	V _R = 400 V f = 1 MHz	T _{VJ} = 25°C	25		pF

		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^\circ C$ repetitive, $I_T = 150 A$ $f = 50 Hz$; $t_p = 200 \mu s$ $I_G = 0.3 A$; $di_G/dt = 0.3 A/\mu s$ $V_D = \frac{2}{3} V_{DRM}$ non-repetitive, $I_T = 80 A$			150	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^\circ C$ $R_{GK} = \infty$; method 1 (linear voltage rise)			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$			1.5	V
I_{GT}	gate trigger current	$V_D = 6 V$ $T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$			1.6	V
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 150^\circ C$			95	mA
I_{GD}	gate non-trigger current				200	mA
I_L	latching current	$t_p = 10 \mu s$ $T_{VJ} = 25^\circ C$ $I_G = 0.3 A$; $di_G/dt = 0.3 A/\mu s$			450	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$ $T_{VJ} = 25^\circ C$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $T_{VJ} = 25^\circ C$ $I_G = 0.5 A$; $di_G/dt = 0.3 A/\mu s$			2	μs
t_q	turn-off time	$V_R = 100 V$; $I_T = 120 A$ $T_{VJ} = 150^\circ C$ $V_D = \frac{2}{3} V_{DRM}$; $t_p = 200 \mu s$ $di/dt = 10 A/\mu s$; $dv/dt = 20 V/\mu s$		150		μs

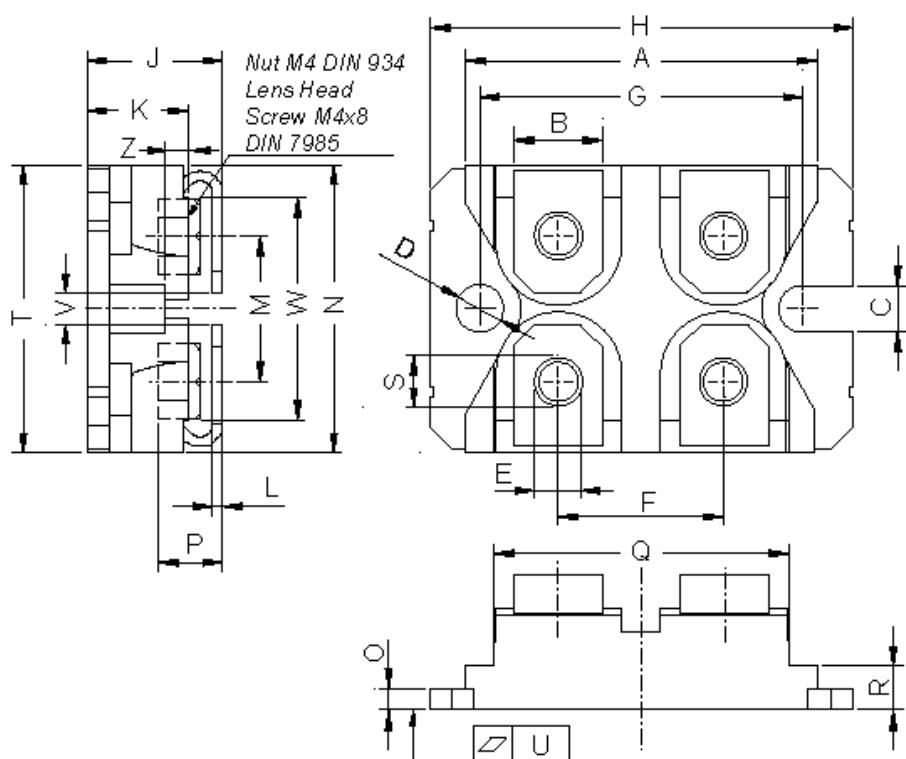
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			150	A
R_{thCH}	thermal resistance case to heatsink			0.10		K/W
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque			1.1	1.5	Nm
M_T	terminal torque			1.1	1.5	Nm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 2500			V
$d_{Spp/App}$	creepage striking distance on surface through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/App}$	creepage striking distance on surface through air	terminal to backside	8.6	6.8		mm

Part number**Product Marking**

C = Thyristor (SCR)
 M = Thyristor
 A = (up to 1800 V)
 80 = Current Rating [A]
 PD = Phase leg, high-side Thyristor / low-side Diode
 1600 = Reverse Voltage [V]
 NA = SOT-227B (minibloc)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	CMA 80 PD 1600 NA	CMA80PD1600NA	Tube	10	509041

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106